

09/605293

FACSIMILE COVER SHEET

TO: Examiner N. Drew Richards, Art Unit 2815

Company: Assistant Commissioner for Patents
Fax No.: 703/872-9319

FROM: Julie G. Cope, Reg. No. 48,624/amm

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Patents, Trademarks and Related Matters

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Applicant : David L. Chapek
Serial No. : 09/605,293
Filed : June 28, 2000
Title : SEMICONDUCTOR DEVICES INCLUDING A LAYER OF
POLYCRYSTALLINE SILICON HAVING A SMOOTH
MORPHOLOGY
Docket : MIO 0037 VA
Art Unit : 2815

Assistant Commissioner for Patents
Washington, DC 20231
Box AF

Sir:

CERTIFICATE OF FACSIMILE TRANSMISSION
I hereby certify that this paper is being facsimile transmitted to the Patent and Trademark
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Julie G. Cope

Reg. No. 48,624

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AMENDMENT AFTER FINAL

This paper is being filed in response to the Office Action mailed on December 16, 2002. Entry of this amendment is requested as it is believed the amendments and remarks place the application in condition for allowance or will at least reduce the number of issues for appeal.

CLEAN VERSION OF THE AMENDMENTS

A version of the amendments showing the markings is provided in a separate appendix attached to this paper.

In the Specification

At page 8, lines 2-13 should read:

With continued reference to Fig. 1, the layer 14 of silicon dioxide 16 is formed on the substrate 12 by an conventional oxidation process or deposition process, and has been doped with hydrogen ions to provide a surface conducive to the deposition of polycrystalline silicon. Depending upon the nature of the layer 14 of silicon dioxide 16, the layer 14 of silicon dioxide 16 can be formed by thermal oxidation, chemical vapor deposition (CVD), low pressure chemical vapor deposition (LPCVD), plasma enhanced